

Silicon Carbide Power MOSFET C3M™ MOSFET Technology N-Channel Enhancement Mode

Features

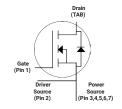
- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant







TO-263-7L XL



Package Types: TO-263-7L XL PN's: C3M0040120J1

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Typical Applications

- Datacenter and telecom power supplies
- EV battery chargers
- High voltage DC/DC converters
- Energy storage systems
- Solar inverters

Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Key Parameters

Parameter	Symbol	Min.	Тур.	Max	Unit	Conditions	Note
Drain - Source Voltage	V _{DS}			1200		T _c = 25°C	
Maximum Gate - Source Voltage	V _{GS(max)}	-8		+19	v	Transient	
Operational Gate-Source Voltage	V _{GS op}		-4/15			Static	Note 1
DC Continuous Drain Current				64	A	V _{GS} = 15 V, T _C = 25 °C, T _J ≤150 °C	Fig. 19 Note 2
	I _D			42		V _{GS} = 15 V, T _C = 100 °C, T _J ≤150 °C	
Pulsed Drain Current	I _{DM}			100		t _{Pmax} limited by T _{jmax} V _{GS} = 15V, T _C = 25 °C	Fig. 22
Power Dissipation	P _D			272	W	$T_c = 25^{\circ} C, T_J = 150^{\circ} C$	Fig. 20
Operating Junction Temperature	T _J			-40 to +175			
Case and Storage Temperature	T_c , T_{stg}			-40 to 150	°C		
Solder Temperature	T _L			260		According to JEDEC J-STD-020	

Note (1): Recommended turn-on gate voltage is 15V with ±5% regulation tolerance, see Application Note PRD-04814 for additional details

Note (2): Verified by design

Electrical Characteristics ($T_c = 25$ °C Unless Otherwise Specified)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	Note	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200				$V_{GS} = 0 \text{ V, I}_{D} = 100 \mu\text{A}$		
Gate Threshold Voltage		1.8	2.7	3.6	V	$V_{DS} = V_{GS}, I_{D} = 9.2 \text{ mA}$	Eig 11	
	$V_{GS(th)}$		2.2			$V_{DS} = V_{GS}, I_{D} = 9.2 \text{ mA}, T_{J} = 150 \text{ °C}$	Fig. 11	
Zero Gate Voltage Drain Current	I _{DSS}		1	50	μА	V _{DS} = 1200 V, V _{GS} = 0 V		
Gate-Source Leakage Current	I _{GSS}		10	250	nA	V _{GS} = 15 V, V _{DS} = 0 V		
			40	53.5	mΩ	$V_{GS} = 15 \text{ V}, I_D = 33.3 \text{ A}$	Fig. 4,	
Drain-Source On-State Resistance	R _{DS(on)}		60			V _{GS} = 15 V, I _D = 33.3 A, T _J = 150 °C	5,6	
			21		_	V _{DS} = 20 V, I _{DS} = 33.3 A		
Transconductance	g _{fs}		20		S	V _{DS} = 20 V, I _{DS} = 33.3 A, T _J = 150 °C	Fig. 7	
Input Capacitance	C _{iss}		2900				Fig. 17, 18	
Output Capacitance	C _{oss}		103		pF	$V_{GS} = 0 \text{ V}, V_{DS} = 1000 \text{ V}$		
Reverse Transfer Capacitance	C _{rss}		5			$f = 100 \text{ kHz}$ $V_{AC} = 25 \text{ mV}$		
C _{oss} Stored Energy	E _{oss}		60		μJ		Fig. 16	
Turn-On Switching Energy (Body Diode FWD)	E _{on}		339		1	$V_{DS} = 800 \text{ V}, V_{GS} = -4 \text{ V}/15 \text{ V},$	Fig. 26	
Turn-Off Switching Energy (Body Diode FWD)	E _{OFF}		67		μJ	$I_D = 33.3 \text{ A},$ $R_{G(ext)} = 2.5 \Omega, L = 99 \mu H$		
Turn-On Delay Time	t _{d(on)}		13					
Rise Time	t _r		18			$V_{DD} = 800 \text{ V}, V_{GS} = -4 \text{ V}/15 \text{ V}$	Fig. 27	
Turn-Off Delay Time	t _{d(off)}		22		ns	$R_{G(ext)} = 2.5 \Omega$, $I_D = 33.3 A$, $L = 99$ Timing Relative to V_{DS} , Inductive Load		
Fall Time	t _f		8					
Internal Gate Resistance	R _{G(int)}		3.5		Ω	f = 1 MHz, V _{AC} = 25 mV		
Gate to Source Charge	Q _{gs}		35				Fig. 12	
Gate to Drain Charge	Q _{gd}		27		nC	$V_{DS} = 800 \text{ V}, V_{GS} = -4 \text{ V}/15 \text{ V}$ $I_D = 33.3 \text{ A}$		
Total Gate Charge	Q_{g}		94			Per IEC60747-8-4 pg 21		

Reverse Diode Characteristics (T_C = 25 °C Unless Otherwise Specified)

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Note	
Diode Forward Voltage	V	5.5		V	$V_{GS} = -4 \text{ V, I}_{SD} = 20 \text{ A, T}_{J} = 25 \text{ °C}$	Fig. 8, 9, 10	
	V _{SD}	4.5	V	$V_{GS} = -4 \text{ V}, I_{SD} = 20 \text{ A}, T_{J} = 150 \text{ °C}$	Fig. 8, 9, 10		
Continuous Diode Forward Current	Is		44		V _{GS} = -4 V, T _C = 25 °C		
Diode Pulse Current	I _{S, pulse}		100	A	V_{GS} = -4 V, Pulse Width t_p Limited by T_{jmax}		
Reverse Recovery Time	t _{rr}	11		ns			
Reverse Recovery Charge	Q _{rr}	323		nC	$V_{GS} = -4 \text{ V}, I_{SD} = 33.3 \text{ A}, V_{R} = 800 \text{ V}$ $dif/dt = 9890 \text{ A}/\mu\text{s}$		
Peak Reverse Recovery Current	I _{rrm}	52		А			
Reverse Recovery Time	t _{rr}	17		ns			
Reverse Recovery Charge	Q _{rr}	150		nC	$V_{GS} = -4 \text{ V}, I_{SD} = 33.3 \text{ A}, V_{R} = 800 \text{ V}$ dif/dt = 1815 A/ μ s		
Peak Reverse Recovery Current	I _{rrm}	16		А			

Thermal Characteristics

Parameter	Symbol	Тур.	Unit	Test Conditions	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.46	96/14		F' 04
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	40	°C/W		Fig. 21

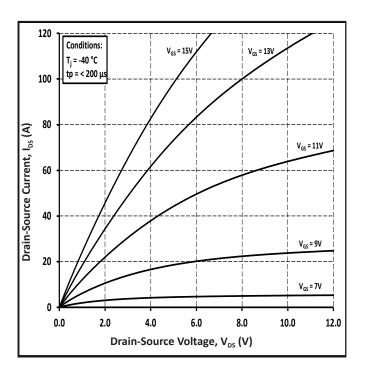


Figure 1. Output Characteristics T₁ = -40 °C

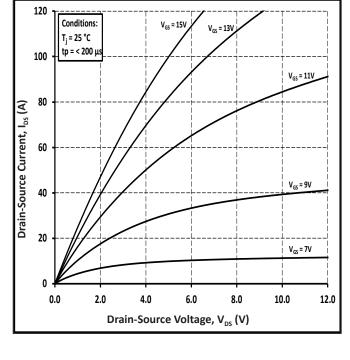


Figure 2. Output Characteristics T_J = 25 °C

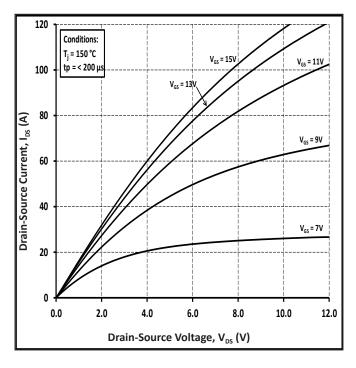


Figure 3. Output Characteristics T_J = 150 °C

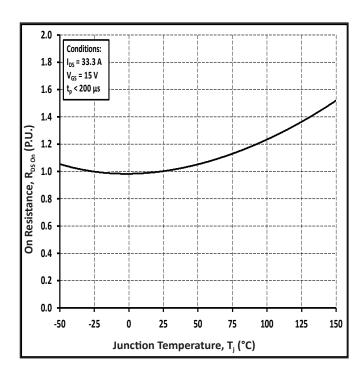


Figure 4. Normalized On-Resistance vs Temperature

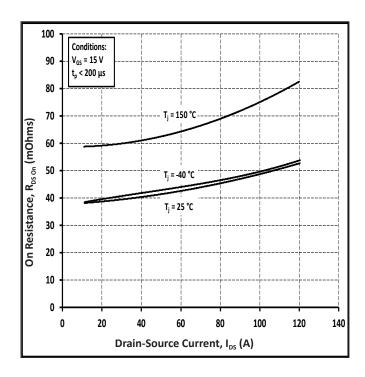


Figure 5. On-Resistance vs Drain Current for Various Temperatures

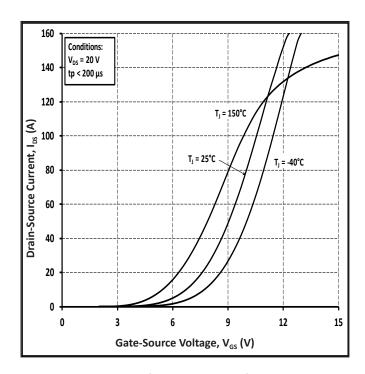


Figure 7. Transfer Characteristic for Various Junction Temperatures

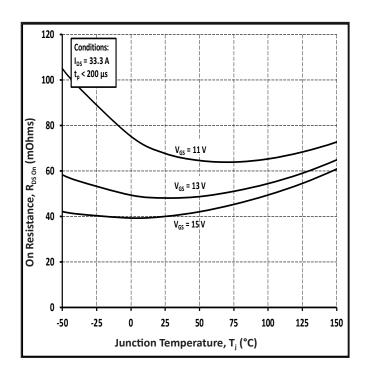


Figure 6. On-Resistance vs Temperature for Various Gate Voltage

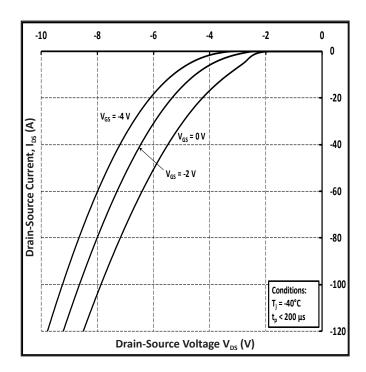


Figure 8. Body Diode Characteristic at -40 °C

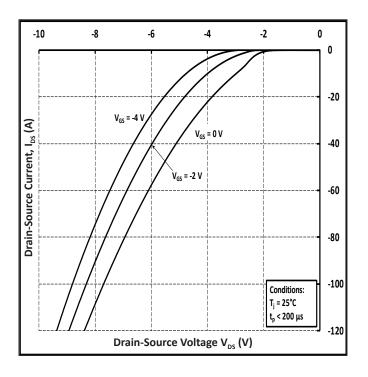


Figure 9. Body Diode Characteristic at 25 °C

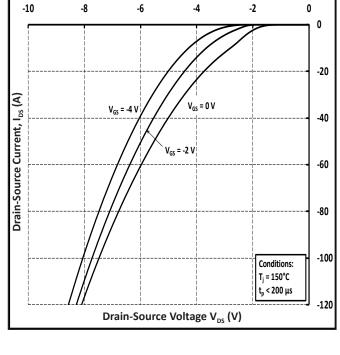


Figure 10. Body Diode Characteristic at 150 °C

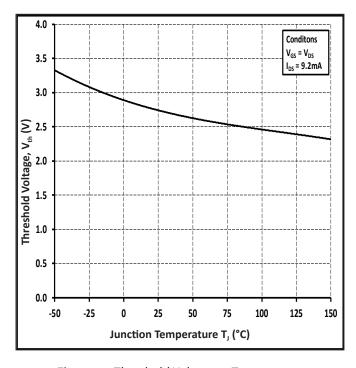


Figure 11. Threshold Voltage vs Temperature

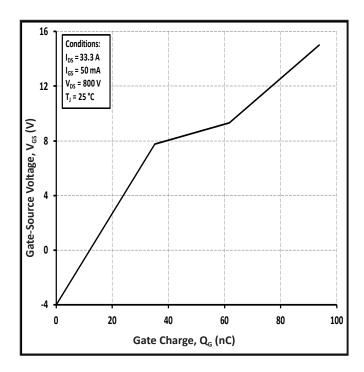


Figure 12. Gate Charge Characteristic

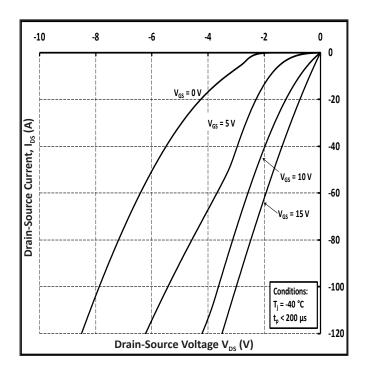


Figure 13. 3rd Quadrant Characteristic at -40 °C

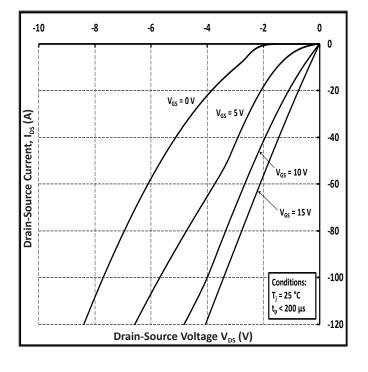


Figure 14. 3rd Quadrant Characteristic at 25 °C

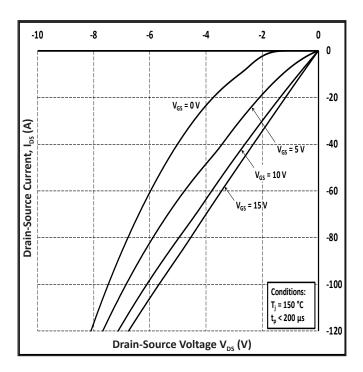


Figure 15. 3rd Quadrant Characteristic at 150 °C

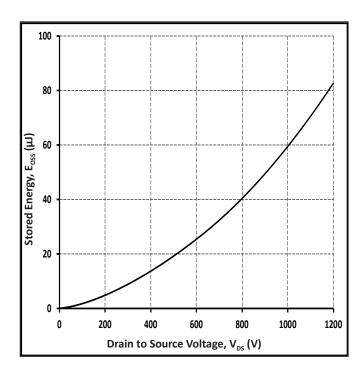
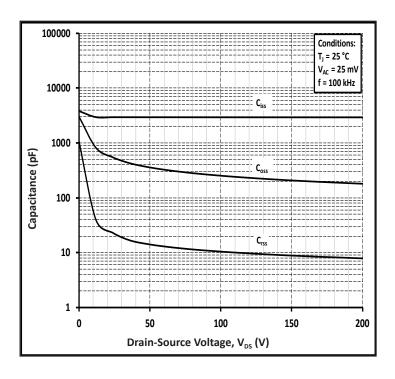


Figure 16. Output Capacitor Stored Energy



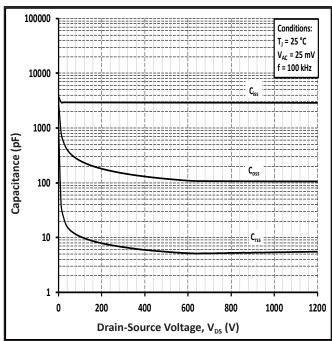


Figure 17. Capacitances vs Drain-Source Voltage (0-200 V)

Figure 18. Capacitances vs Drain-Source Voltage (0-1200 V)

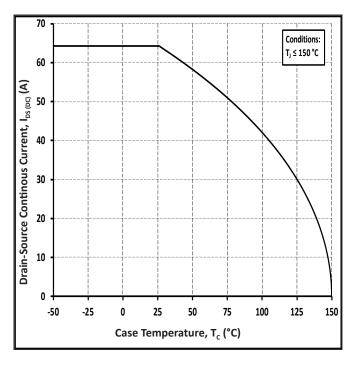


Figure 19. Continuous Drain Current Derating vs Case Temperature

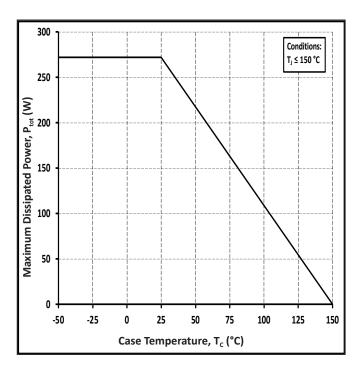


Figure 20. Maximum Power Dissipation Derating vs Case Temperature

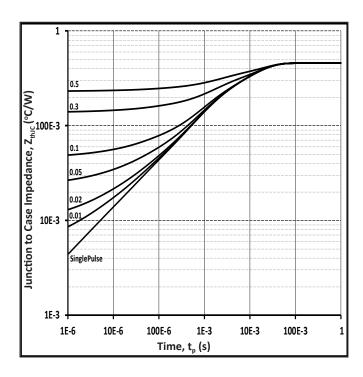


Figure 21. Transient Thermal Impedance (Junction - Case)

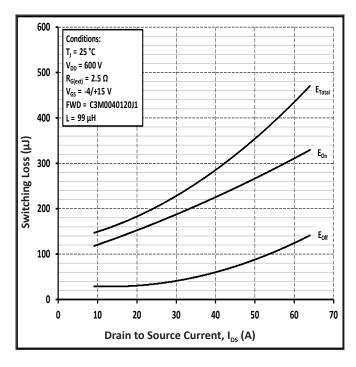


Figure 23. Clamped Inductive Switching Energy vs Drain Current (V_{DD} = 600 V)

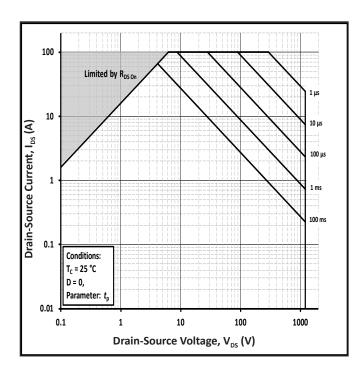


Figure 22. Safe Operating Area

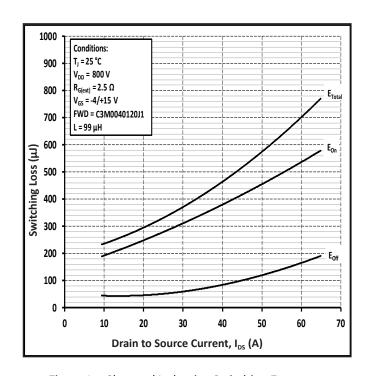


Figure 24. Clamped Inductive Switching Energy vs Drain Current ($V_{DD} = 800 \text{ V}$)

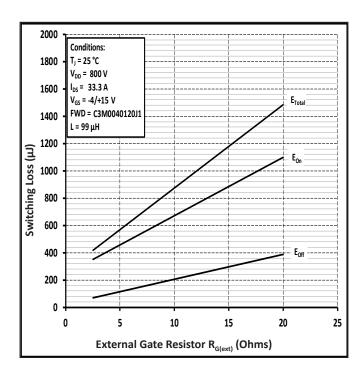


Figure 25. Clamped Inductive Switching Energy vs $R_{G(ext)}$

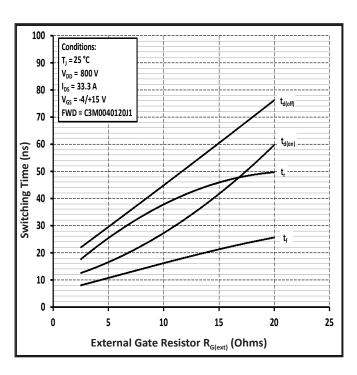


Figure 27. Switching Times vs R_{G(ext)}

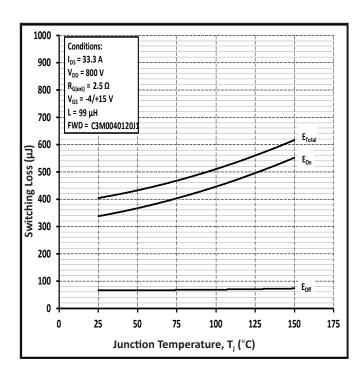


Figure 26. Clamped Inductive Switching Energy vs Temperature

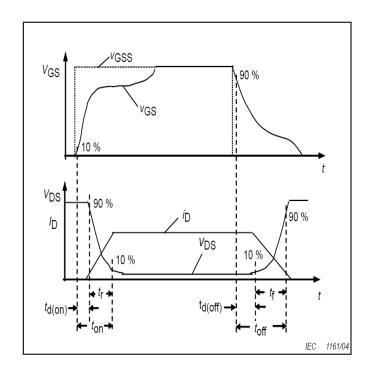


Figure 28. Switching Times Definition

Test Circuit Schematic

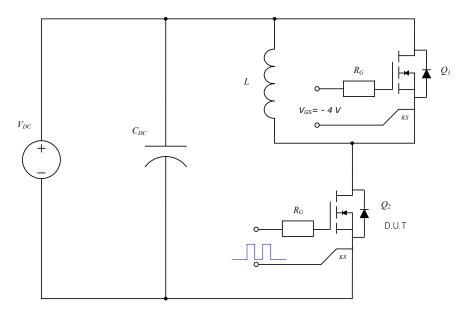
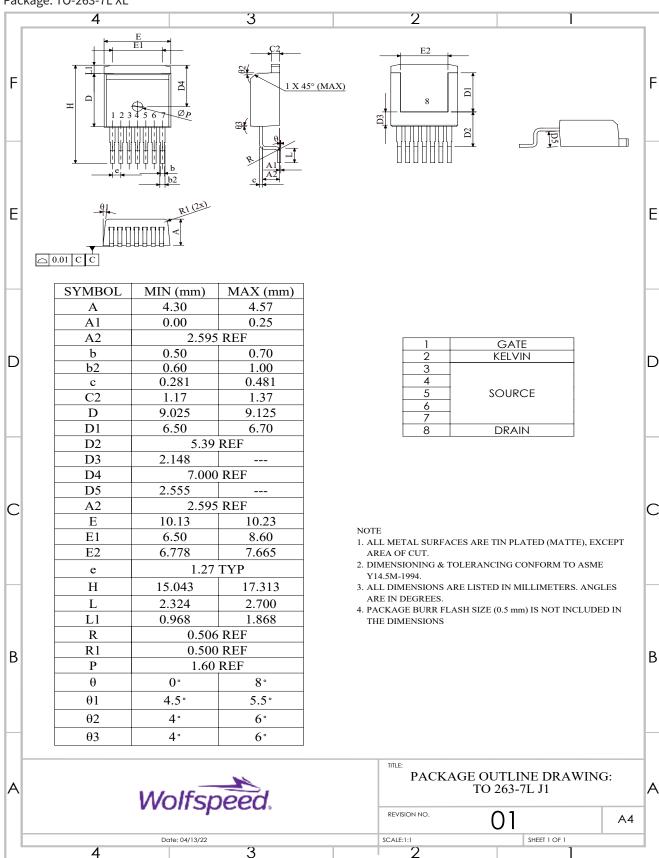


Figure 29. Clamped Inductive Switching Waveform Test Circuit

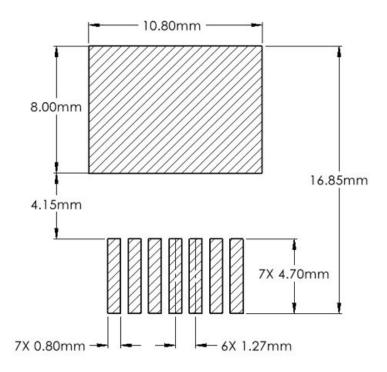
Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET body diode as shown above.

Package Dimensions

Package: TO-263-7L XL



Recommended Solder Pad Layout



Revision History

Current Revision	Date of Release	Description of Changes
0	October-2021	Initial Release
1	N/A	Not Released
2	November-2023	Updated Wolfspeed branding, package drawing, package image, solder pad layout, added Rev history, Table 1 layout revised
3	December - 2024	Legal Disclaimer Updated

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